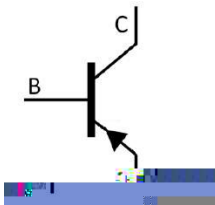


Rev.E Mar.-2016

KF \$O) GE G Silicon PNP transistor in a TO-92 Plastic Package.

)J: (*(.
 Complementary pair with 2SC1317.

AF output amplifier and driver.



PIN1 Base PIN 2 Collector PIN 3 Emitter

h_{FE} Classifications Symbol	Q	R	S
h_{FE} Range	85~170	120~240	170~340

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-500	mA
Collector Current – Continuous(Pulse)	I_{CP}	-1.0	A
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

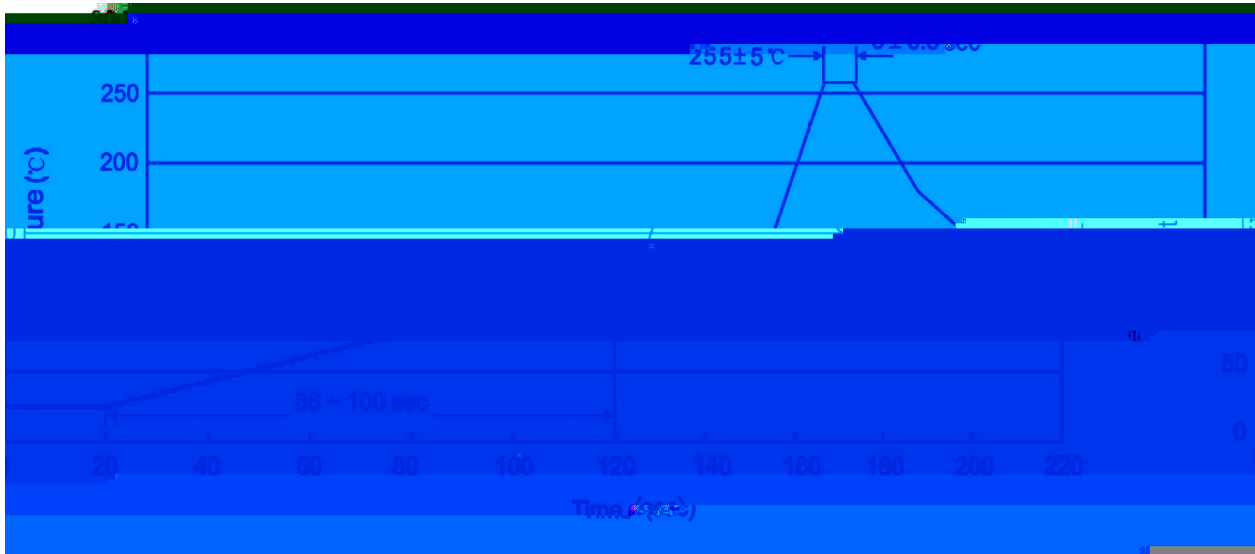
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-10\mu A$ $I_E=0$	-30			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-10mA$ $I_B=0$	-25			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-10\mu A$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-20V$ $I_E=0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-10V$ $I_C=-150mA$	85		340	
	$h_{FE(2)}$	$V_{CE}=-10V$ $I_C=-500mA$	40			

Collector to Emitter Saturation





- 9| 1
- 8. (0
- H1 h_{FE}
- !!!!
- Note:
- BR: Company Code.
- A719: Product Type.
- Q: h_{FE} Classifications Symbol
- ****: Lot No. Code,code change with Lot No.



- | | | | | |
|---|--------|-----|------------|--------|
| 1 | 25 | 150 | 60 | 90sec; |
| 2 | 255..5 | | 5..0.5sec; | |
| 3 | | 2 | 10 | /sec. |

Note:

1. Preheating: 25~150 , Time: 60~90sec.
2. Peak Temp.: 255..5 , Duration: 5..0.5sec.
3. Cooling Speed: 2~10 /sec.

270..5

10..1 sec.

Temp: 270±5

Time: 10±1 sec

/ BULK

~~dB 9.01~~